MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

TK58E06N1

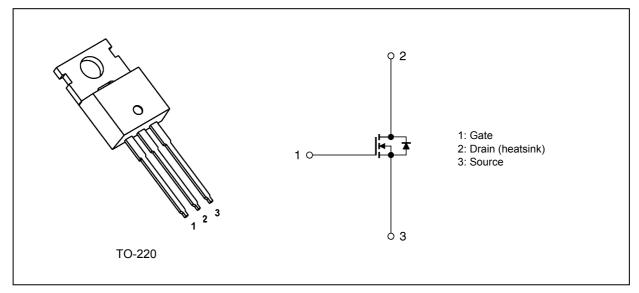
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)}$ = 4.4 m Ω (typ.) (V_{GS} = 10 V)
- (2) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 60 \ V)$
- (3) Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_{D} = 0.5 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics				Rating	Unit
Drain-source voltage			V _{DSS}	60	V
Gate-source voltage			V _{GSS}	±20	1
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I _D	105	Α
Drain current (DC)		(Note 1), (Note 3)	I _D	58	1
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I _{DP}	268	1
Power dissipation	(T _c = 25°C)		PD	110	W
Single-pulse avalanche energy		(Note 4)	E _{AS}	158	mJ
Avalanche current			I _{AR}	58	Α
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150]

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	1.13	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	83.3	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Limited by silicon chip capability. Package limit is 100A.

Note 3: Device mounted with heatsink so that $R_{th(ch-a)}$ becomes 3.57°C/W.

Note 4: V_DD = 48 V, T_ch = 25°C (initial), L = 36.1 μ H, I_{AR} = 58 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

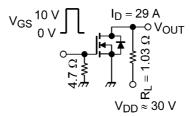
6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_	_	±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	-	—	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	60		_	V
Drain-source breakdown voltage (Note 5)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	45	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.5 mA	2.0	—	4.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 29 A	_	4.4	5.4	mΩ

Note 5: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz	_	3400		pF
Reverse transfer capacitance	C _{rss}		_	45		
Output capacitance	C _{oss}		_	1120		
Gate resistance	r _g	—	_	2.6		Ω
Switching time (rise time)	tr	See Figure 6.2.1.	_	11		ns
Switching time (turn-on time)	t _{on}		_	33		
Switching time (fall time)	t _f		_	17	_	
Switching time (turn-off time)	t _{off}		_	56	_	



 $Duty \le 1\%, \ t_w = 10 \ \mu s$ Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 48$ V, V_{GS} = 10 V, I_D = 58 A	—	46	—	nC
Gate-source charge 1	Q _{gs1}		_	15	_	
Gate-drain charge	Q _{gd}		_	11	_	
Gate switch charge	Q _{SW}		_	17	_	

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 6)	I _{DR}	—	_	_	58	А
Reverse drain current (pulsed)	(Note 6)	I _{DRP}	—	_	—	268	
Diode forward voltage		V_{DSF}	I_{DR} = 58 A, V_{GS} = 0 V	—	—	-1.2	V
Reverse recovery time	(Note 7)	t _{rr}	I _{DR} = 58 A, V _{GS} = 0 V	_	63	_	ns
Reverse recovery charge	(Note 7)	Q _{rr}	-dI _{DR} /dt = 100 A/µs		100		nC

Note 6: Ensure that the channel temperature does not exceed 150°C. Note 7: Ensure that V_{DS} peak does not exceed V_{DSS} .

7. Marking

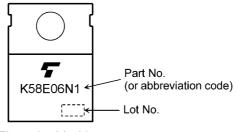
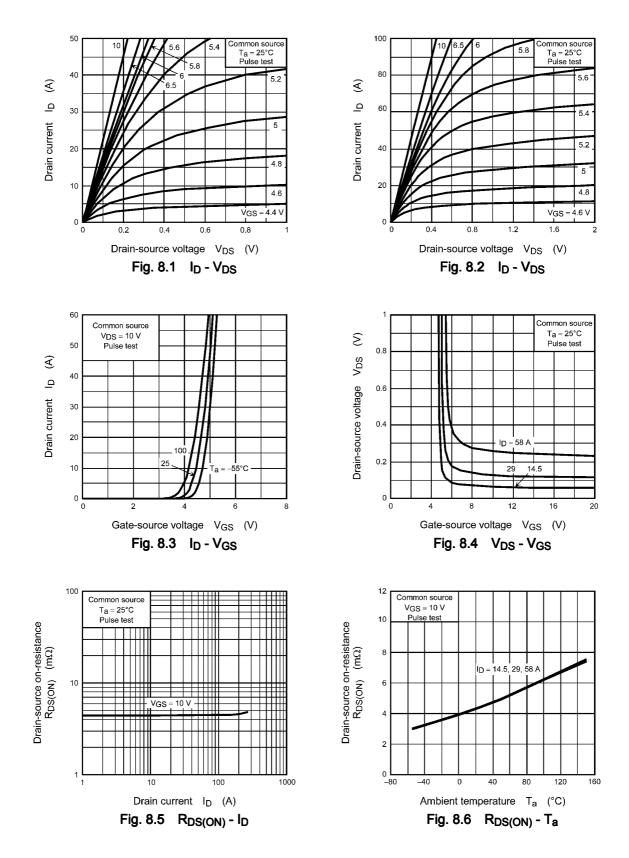
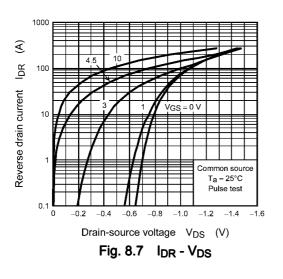


Fig. 7.1 Marking

8. Characteristics Curves (Note)





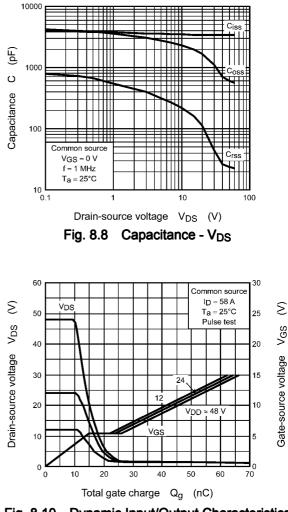
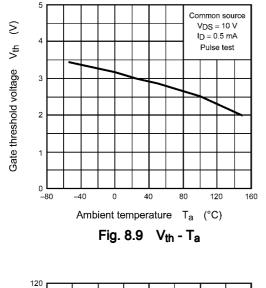
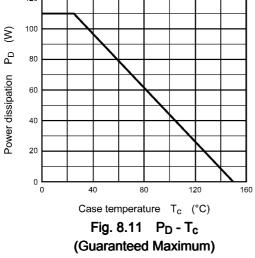
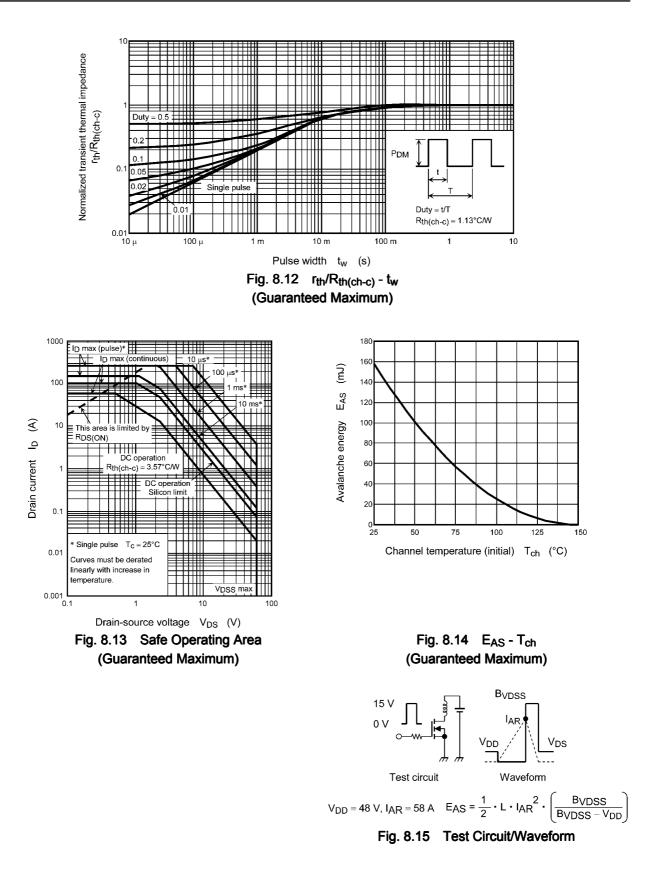


Fig. 8.10 Dynamic Input/Output Characteristics







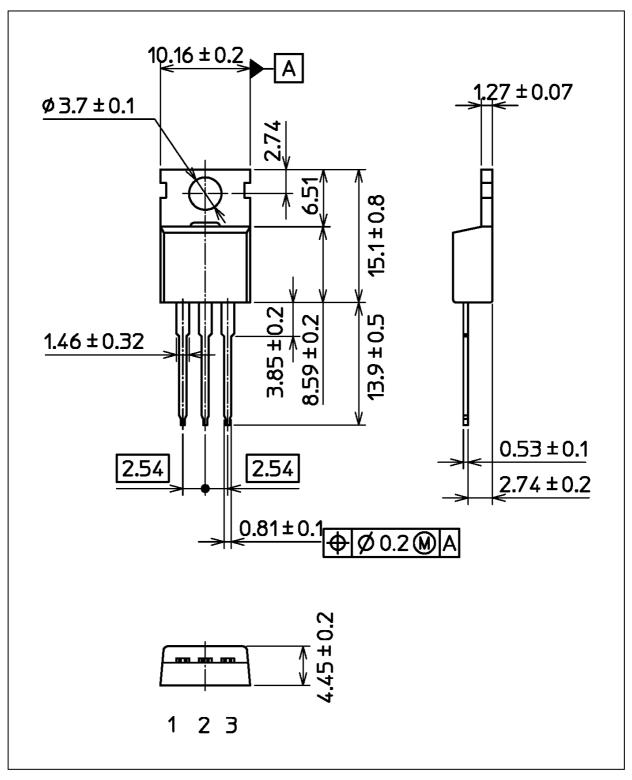
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

TK58E06N1

Unit: mm



Weight: 1.93 g (typ.)

Package Name(s)

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